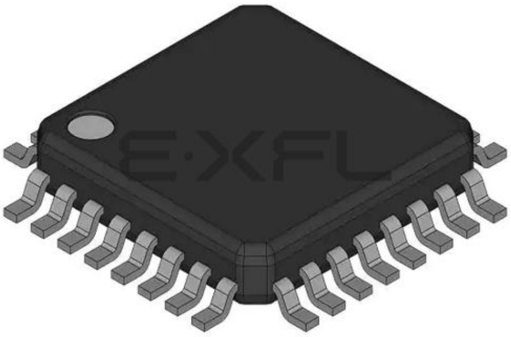
Freescale Semiconductor - MKL05Z16VLC4 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 14x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mkl05z16vlc4

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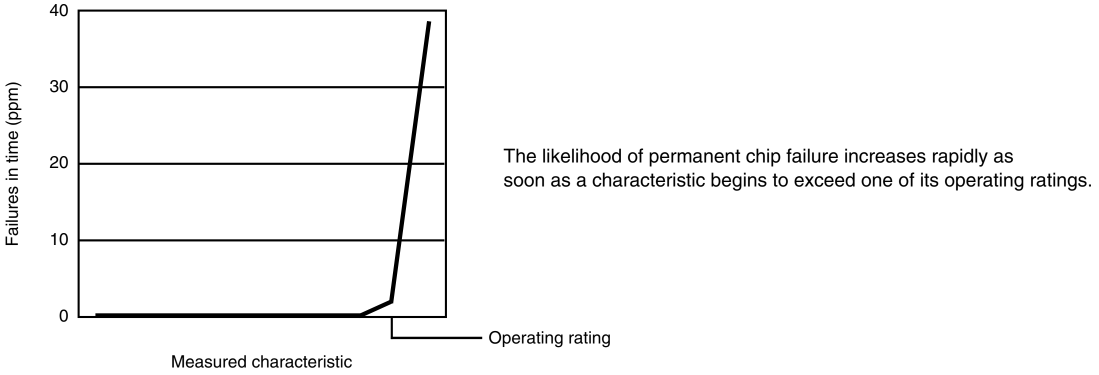
3.4.1 Example

This is an example of an operating rating:

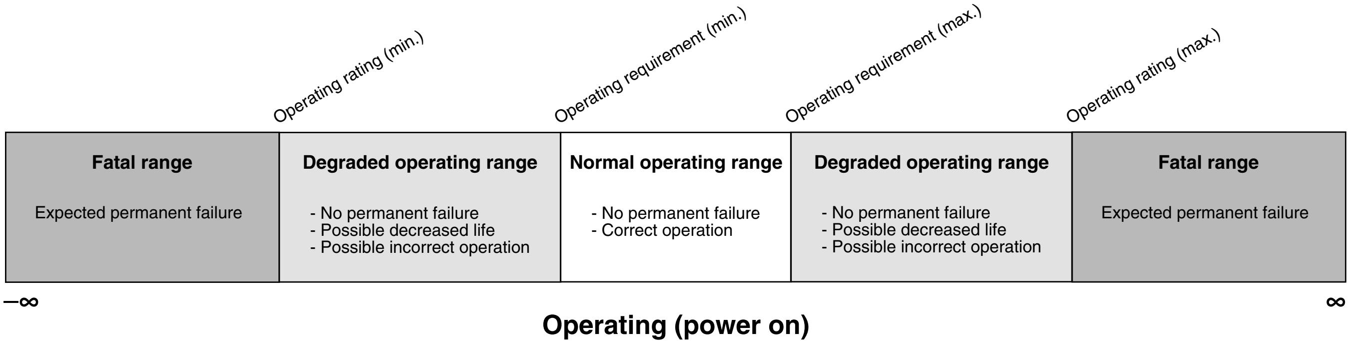
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

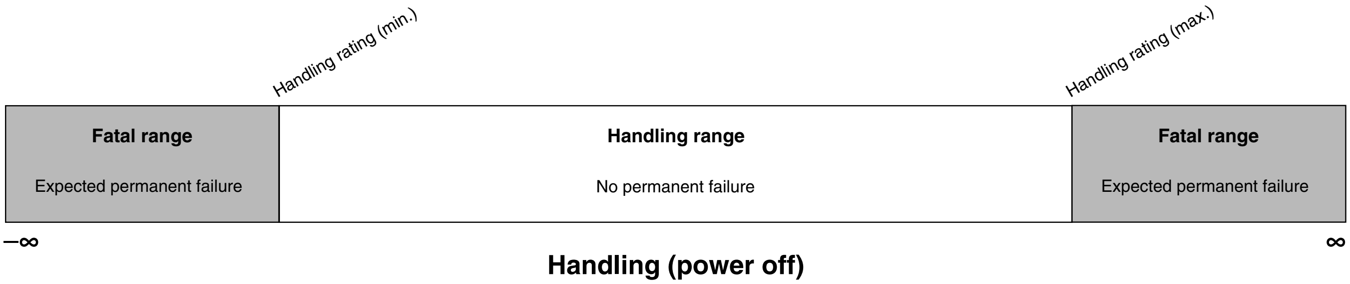
3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements





4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.

4.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{DIO}	Digital pin input voltage (except $\overline{\text{RESET}}$)	–0.3	V_{DD} + 0.3	V
V_{AIO}	Analog pins[1]and $\overline{\text{RESET}}$ pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -5 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -1.5 mA	 V_{DD} – 0.5 V_{DD} – 0.5	 — —	 V V	1
V_{OH}	Output high voltage — High drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -18 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -6 mA	 V_{DD} – 0.5 V_{DD} – 0.5	 — —	 V V	1
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — Normal drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 1.5 mA	 — —	 0.5 0.5	 V V	1
V_{OL}	Output low voltage — High drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 18 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 6 mA	 — —	 0.5 0.5	 V V	1
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range	—	1	μA	2
I_{IN}	Input leakage current (per pin) at 25 °C	—	0.025	μA	2
I_{IN}	Input leakage current (total all pins) for full temperature range	—	41	μA	2
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
R_{PU}	Internal pullup resistors	20	50	kΩ	3

1. PTA12, PTA13, PTB0 and PTB1 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. Measured at V_{DD} = 3.6 V
3. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V • at 25 °C • at 125 °C	 — —	 5.6 6	 6.8 7.2	 mA mA	2, 3
I_{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	3.0	4.2	mA	2
I_{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	2.4	3.36	mA	2
I_{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus • at 3.0 V	—	2.25	3.38	mA	2
I_{DD_VLPRCO}	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code of while(1) loop executing from flash • at 3.0 V	—	182	522	µA	4
I_{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code of while(1) loop executing from flash • at 3.0 V	—	213.33	577.8	µA	4
I_{DD_VLPR}	Very-low-power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code of while(1) loop executing from flash • at 3.0 V	—	242.8	631.8	µA	3, 4
I_{DD_VLPW}	Very-low-power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	106.1	399.42	µA	4

Table continues on the next page...

Table 6. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
$I_{EREFSTEN32KHz}$	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled.							nA
	VLLS1	440	490	540	560	570	580	
	VLLS3	440	490	540	560	570	580	
	LLS	490	490	540	560	570	680	
	VLPS	510	560	560	560	610	680	
	STOP	510	560	560	560	610	680	
I_{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	22	22	22	22	22	22	µA
I_{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	nA
I_{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.							µA
	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	
	OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I_{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents.							µA
	MCGIRCLK (4 MHz internal reference clock)	86	86	86	86	86	86	
	OSCERCLK (4 MHz external crystal)	235	256	265	274	280	287	
I_{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	µA

Table continues on the next page...

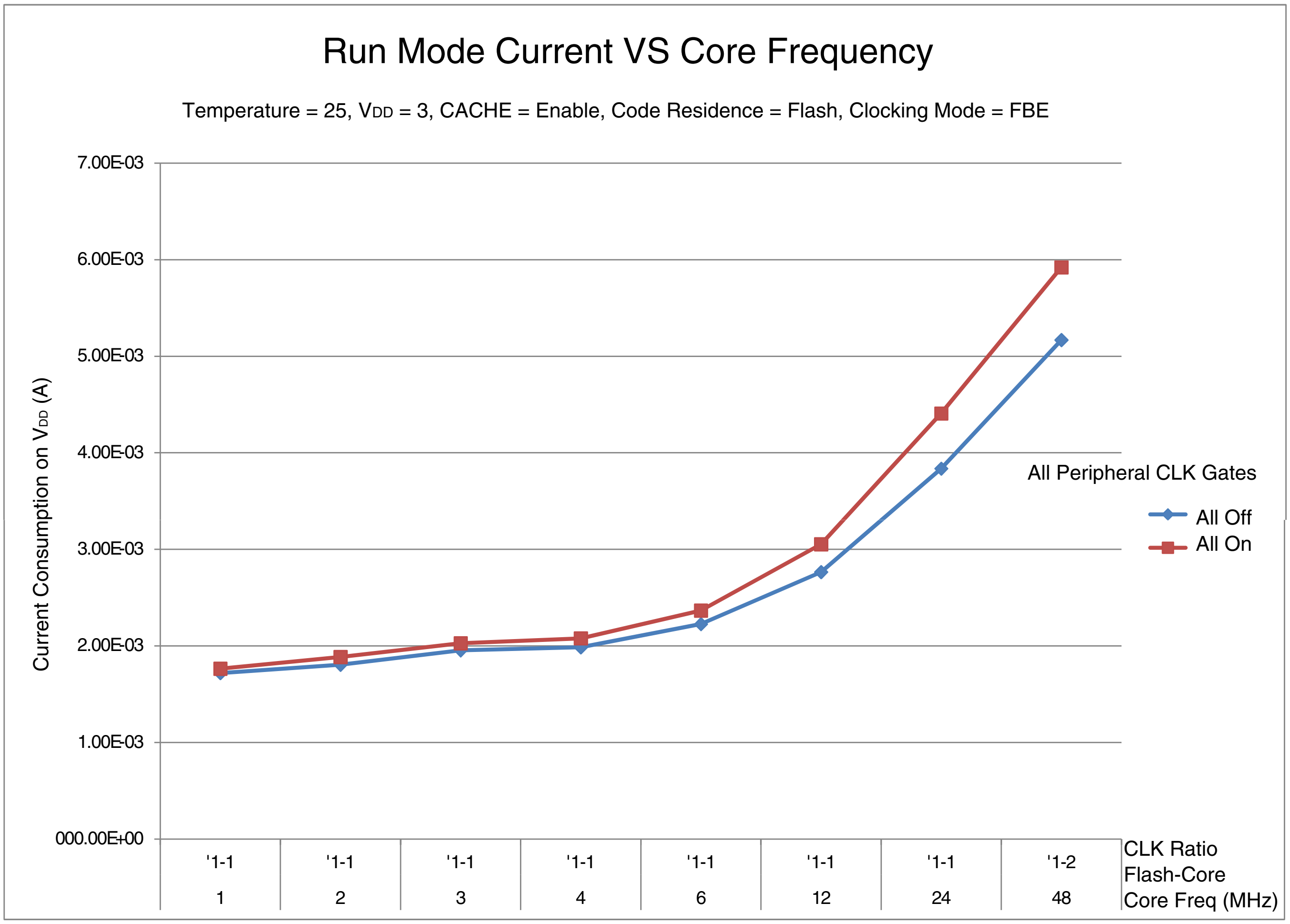


Figure 2. Run mode supply current vs. core frequency

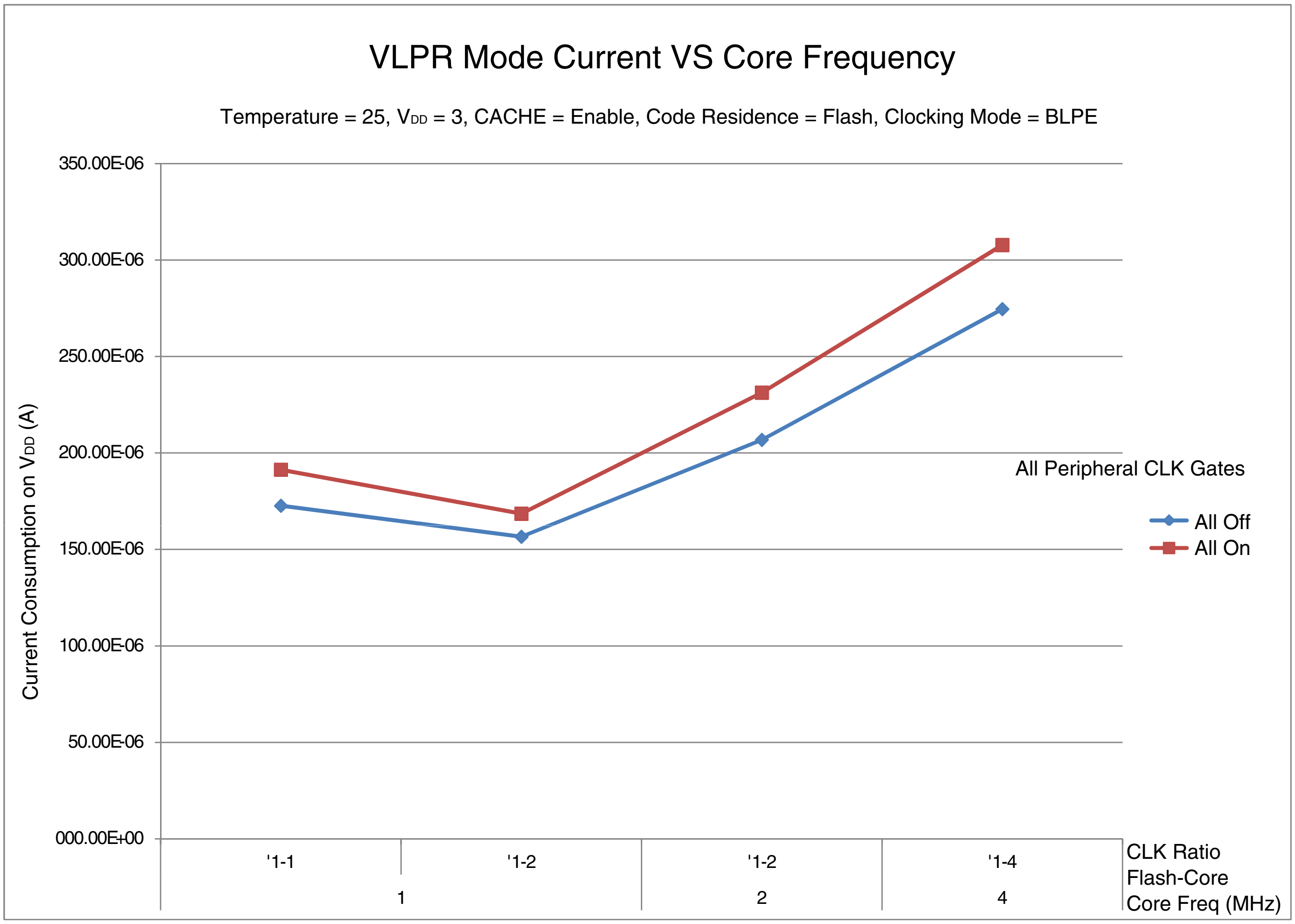


Figure 3. VLPR mode current vs. core frequency

5.2.6 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

5.2.7 Capacitance attributes

Table 7. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	48	MHz	
f_{BUS}	Bus clock	—	24	MHz	
f_{FLASH}	Flash clock	—	24	MHz	
f_{LPTMR}	LPTMR clock	—	24	MHz	
VLPR mode[1]					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	1	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{LPTMR}	LPTMR clock	—	24	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	
f_{LPTMR_pin}	LPTMR clock	—	24	MHz	
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	—	16	MHz	
f_{TPM}	TPM asynchronous clock	—	8	MHz	
f_{UART0}	UART0 asynchronous clock	—	8	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General Switching Specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and I^2C signals.

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
	GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
	Port rise and fall time	—	36	ns	3

1. The greater synchronous and asynchronous timing must be met.
2. This is the shrtest pulse that is guaranteed to be recognized.
3. 75 pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 8. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

5.4.2 Thermal attributes

Table 9. Thermal attributes

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	82	88	97	110	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	58	59	34	42	°C/W	
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	70	74	81	92	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	52	52	28	36	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	13	18	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	27	26	2.3	3.7	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	8	8	8	10	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions —Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions —Junction-to-Board*.

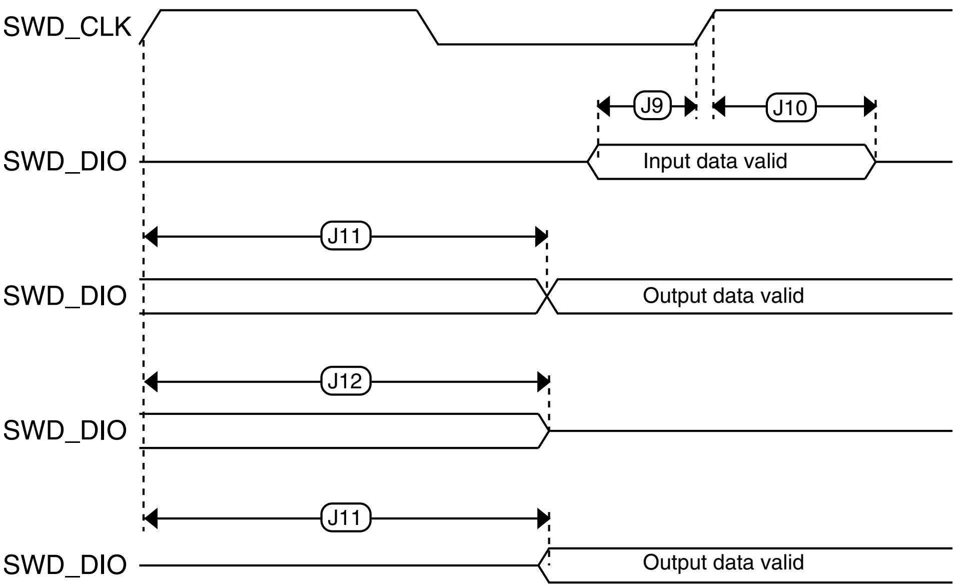


Figure 5. Serial wire data timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

6.3.1 MCG specifications

Table 11. MCG specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C	—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed	31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using SCTRIM and SCFTRIM	—	± 0.3	± 0.6	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature	—	+0.5/-0.7	± 3	$\%f_{dco}$	1, 2

Table continues on the next page...

3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

NOTE

The 32 kHz oscillator works in low power mode by default and cannot be moved into high power/gain mode.

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 14. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 15. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.5	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	55	465	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

6.4.1.3 Flash high voltage current behaviors

Table 16. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 17. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25°C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at $-40°C \leq T_j \leq 125°C$.

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

6.6.1.1 12-bit ADC operating conditions

Table 18. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} - V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS} - V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 8-/10-/12-bit modes	—	4	5	pF	
R_{ADIN}	Input resistance		—	2	5	kΩ	
R_{AS}	Analog source resistance	12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	4
f_{ADCK}	ADC conversion clock frequency	≤ 12-bit mode	1.0	—	18.0	MHz	5
C_{rate}	ADC conversion rate	≤ 12 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.
3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SSA}.
4. This resistance is external to MCU. The analog source resistance must be kept as low as possible to achieve the best results. The results in this data sheet were derived from a system which has < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1ns.
5. To use the maximum ADC conversion clock frequency, the ADHSC bit must be set and the ADLPC bit must be clear.
6. For guidelines and examples of conversion rate calculation, download the ADC calculator tool

Table 19. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
E_Q	Quantization error	- 12-bit modes	—	—	±0.5	LSB[4]	
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	—	1.715	—	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	—	719	—	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25°C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)

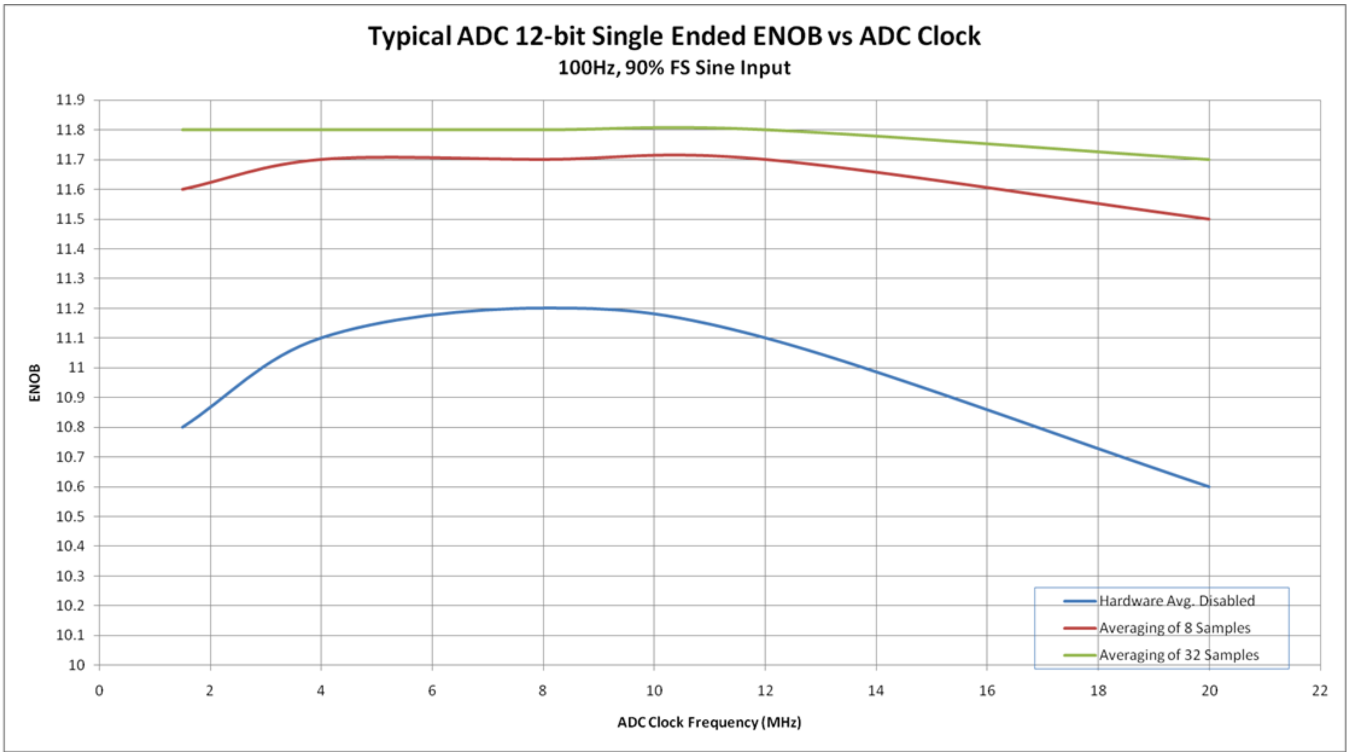


Figure 7. Typical ENOB vs. ADC_CLK for 12-bit single-ended mode

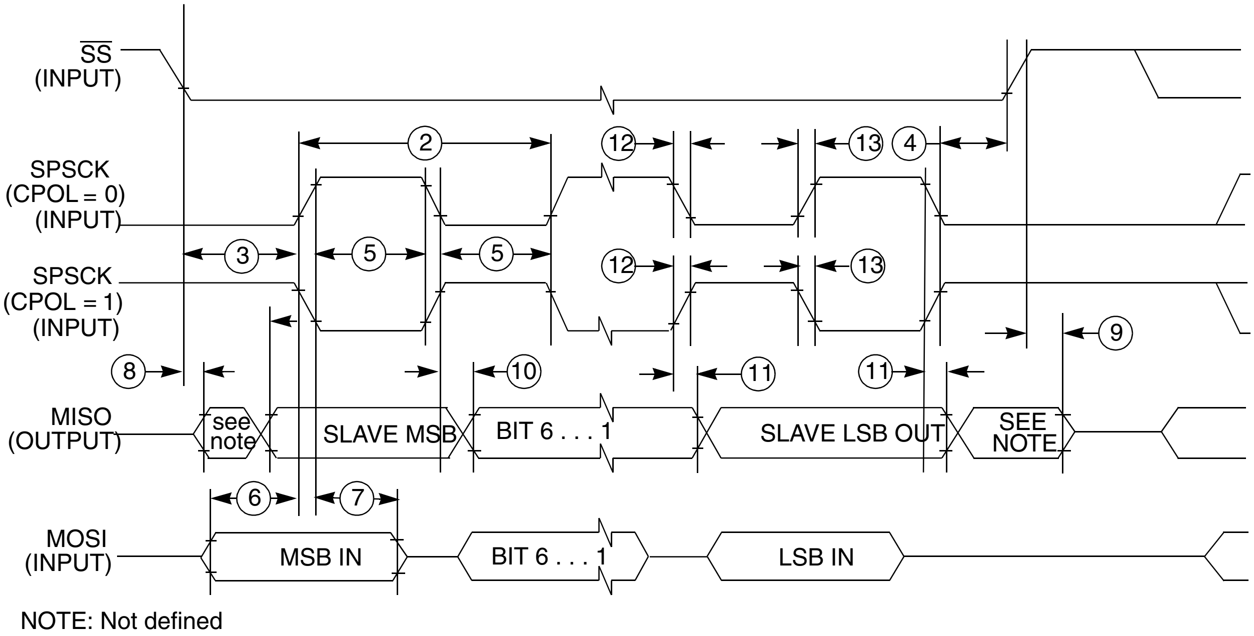


Figure 14. SPI slave mode timing (CPHA = 0)

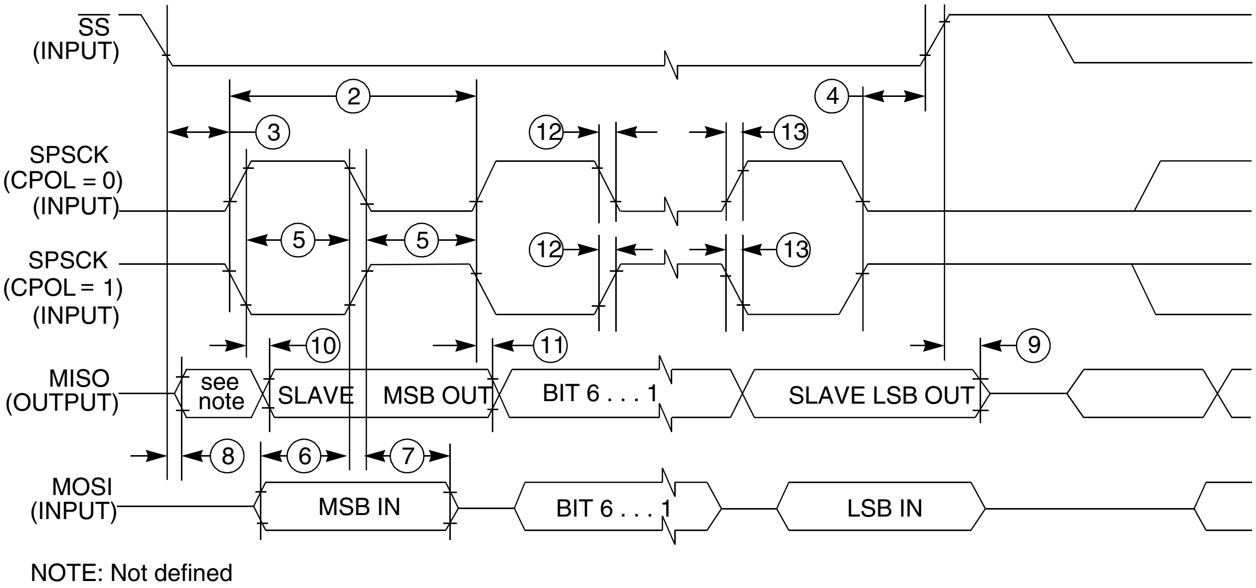


Figure 15. SPI slave mode timing (CPHA = 1)

6.8.2 I^{2}C

See General switching specifications.

6.8.3 UART

See General switching specifications.

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
25	17	17	13	PTB1/ IRQ_9	ADC0_SE5/ TSI0_IN3/ DAC0_OUT/ CMP0_IN3	ADC0_SE5/ TSI0_IN3/ DAC0_OUT/ CMP0_IN3	PTB1/ IRQ_9	UART0_TX	UART0_RX
26	18	18	14	PTB2/ IRQ_10/ LLWU_P5	ADC0_SE4/ TSI0_IN2	ADC0_SE4/ TSI0_IN2	PTB2/ IRQ_10/ LLWU_P5	UART0_RX	UART0_TX
27	19	19	15	PTA8	ADC0_SE3/ TSI0_IN1	ADC0_SE3/ TSI0_IN1	PTA8		
28	20	20	16	PTA9	ADC0_SE2/ TSI0_IN0	ADC0_SE2/ TSI0_IN0	PTA9		
29	—	—	—	PTB20	DISABLED	DISABLED	PTB20		
30	—	—	—	VSS	VSS	VSS			
31	—	—	—	VDD	VDD	VDD			
32	—	—	—	PTB14/ IRQ_11	DISABLED	DISABLED	PTB14/ IRQ_11	EXTRG_IN	
33	21	21	—	PTA10/ IRQ_12	DISABLED	TSI0_IN11	PTA10/ IRQ_12		
34	22	22	—	PTA11/ IRQ_13	DISABLED	TSI0_IN10	PTA11/ IRQ_13		
35	23	23	17	PTB3/ IRQ_14	DISABLED	DISABLED	PTB3/ IRQ_14	I2C0_SCL	UART0_TX
36	24	24	18	PTB4/ IRQ_15/ LLWU_P6	DISABLED	DISABLED	PTB4/ IRQ_15/ LLWU_P6	I2C0_SDA	UART0_RX
37	25	25	19	PTB5/ IRQ_16	NMI_b	ADC0_SE1/ CMP0_IN1	PTB5/ IRQ_16	TPM1_CH1	NMI_b
38	26	26	20	PTA12/ IRQ_17/ LPTMR0_ALT2	ADC0_SE0/ CMP0_IN0	ADC0_SE0/ CMP0_IN0	PTA12/ IRQ_17/ LPTMR0_ALT2	TPM1_CH0	TPM_CLKIN0
39	27	27	—	PTA13	TSI0_IN9	TSI0_IN9	PTA13		
40	28	28	—	PTB12	TSI0_IN8	TSI0_IN8	PTB12		
41	—	—	—	PTA19	DISABLED	DISABLED	PTA19		SPI0_SS_b
42	—	—	—	PTB15	DISABLED	DISABLED	PTB15	SPI0_MOSI	SPI0_MISO
43	—	—	—	PTB16	DISABLED	DISABLED	PTB16	SPI0_MISO	SPI0_MOSI
44	—	—	—	PTB17	DISABLED	DISABLED	PTB17	TPM_CLKIN1	SPI0_SCK
45	29	29	21	PTB13	ADC0_SE13	ADC0_SE13	PTB13	TPM1_CH1	RTC_CLKOUT
46	30	30	22	PTA0/ IRQ_0/ LLWU_P7	SWD_CLK	ADC0_SE12/ CMP0_IN2	PTA0/ IRQ_0/ LLWU_P7	TPM1_CH0	SWD_CLK
47	31	31	23	PTA1/ IRQ_1/ LPTMR0_ALT1	RESET_b	DISABLED	PTA1/ IRQ_1/ LPTMR0_ALT1	TPM_CLKIN0	RESET_b
48	32	32	24	PTA2	SWD_DIO	DISABLED	PTA2	CMP0_OUT	SWD_DIO

8.2 KL05 Pinouts

The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

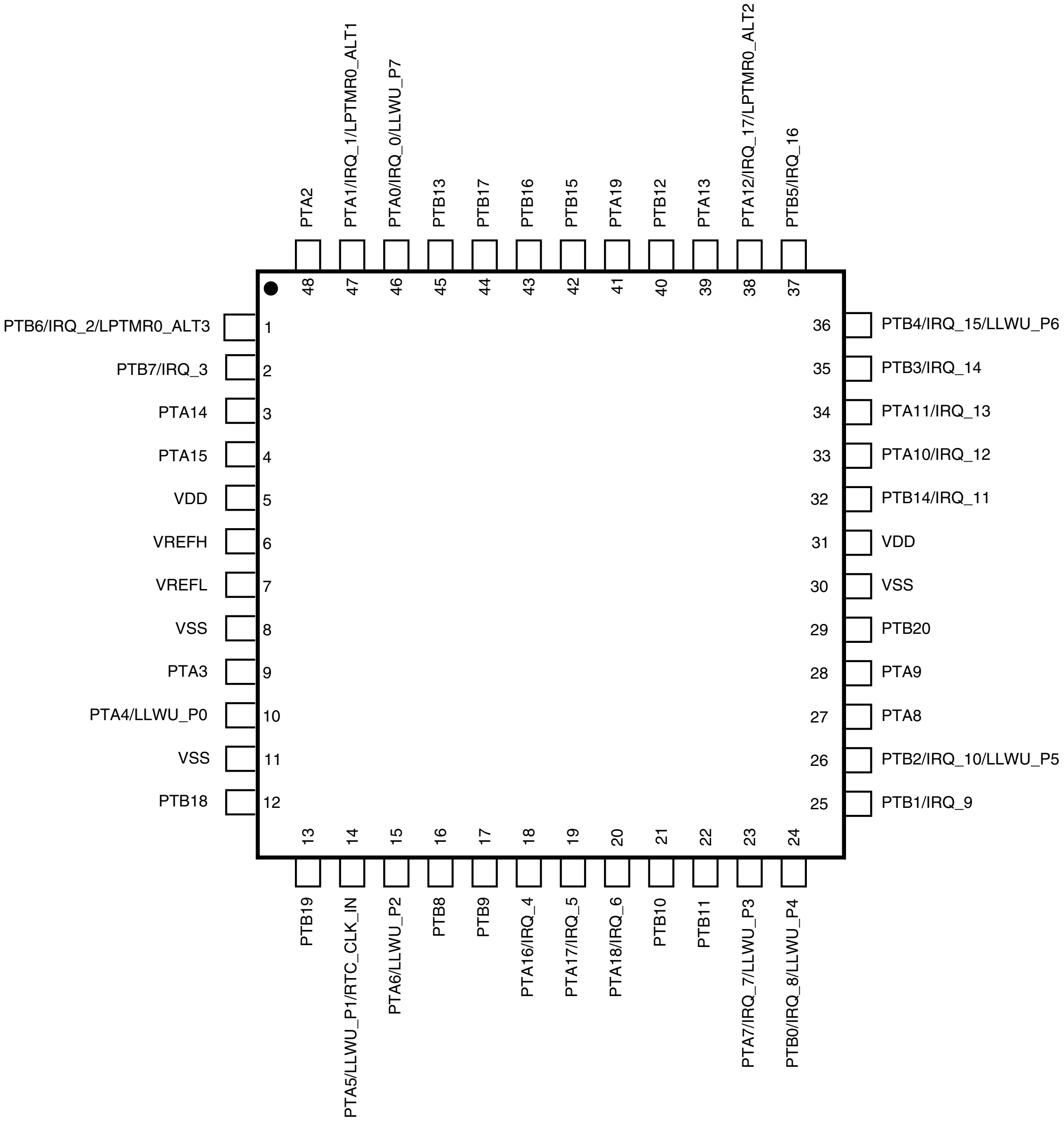


Figure 16. KL05 48-pin LQFP pinout diagram

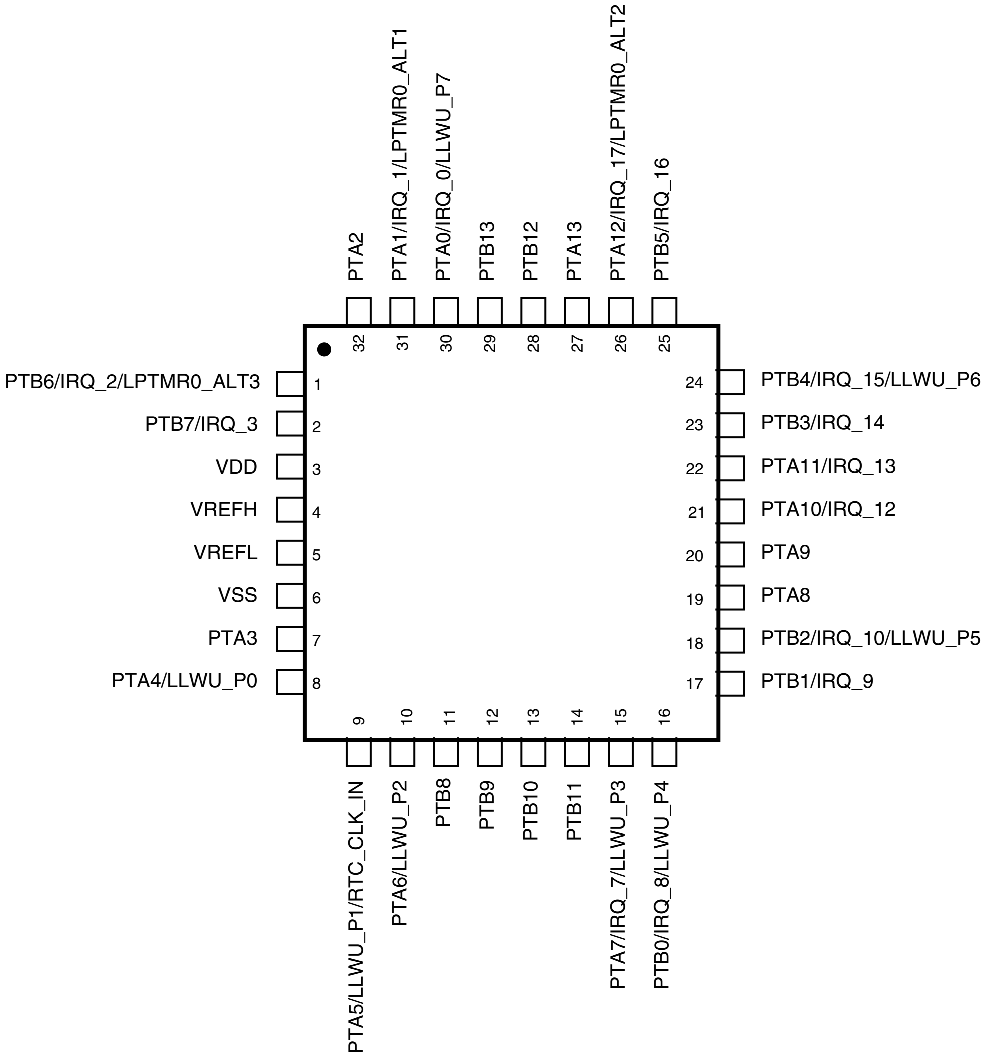


Figure 17. KL05 32-pin LQFP pinout diagram

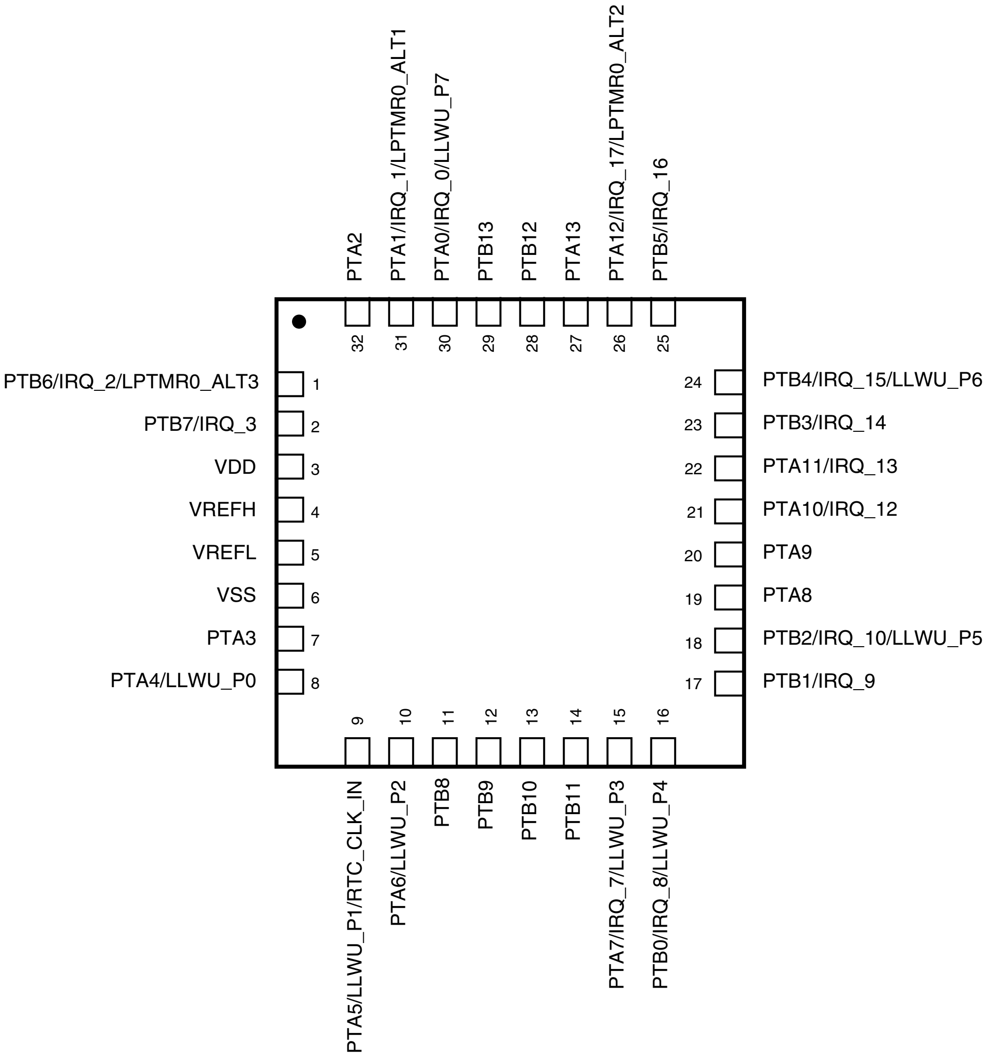


Figure 18. KL05 32-pin QFN pinout diagram